

The R3 Model: Verilog-A Code

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Initial Comments

- Modeling people generally have device/physics background
 - occasionally design (e.g. EKV, Prof. Tsividis)
- Models are really software, model developers:
 - must understand how models and simulators interact
 - must follow standard (good) software practices
 - style
 - source-code control
 - regression testing (automated QA)
 - develop tests in parallel with model
 - documentation
 - structured release practices
- Historic issue: PhD/papers based on physics, not code





Most Common Errors in Compact Model Codes

- Used to be in hand-generated derivatives
 - problem completely removed by use of Verilog-A
- Now is handling of "book-keeping" things
 - polarity flipping (e.g. PMOS instead of NMOS)
 - terminal swapping (e.g. symmetric drain and source)
 - scale (e.g. mapping of netlisted microns to meters)
 - shrink
 - mutiplicity factor
- Last of these automated in Verilog-A, except for mismatch
- Automated QA can do the rest





Generic Issues with Compact Model Codes

- Hand-coded C used to impose a huge barrier to anyone wanting to develop a compact model
- Verilog-A significantly lowered that barrier
 - but does not come with a "bozo filter" to prevent bad code
- People read Verilog-A LRM then think they are an expert
 - universally don't read existing best practices
 - universally repeat common mistakes
- Will not cover details here
 - more "don'ts" than "do's"
 - list of "don'ts" expanding all the time
 - updated best practices document in preparation
 - IEEE EDS CM-TAC





R3 Code is Split Into Four Parts

- Two intended to be generic
 - generalMacrosAndDefines.va
 - junctionMacros.va
- Two specific to r3
 - top-level model code in r3.va
 - detailed core calculations in r3Macros.va
- This was done so
 - core r3 calculations can be used as a building block for other models (e.g. LDMOS)
 - nitty-gritty details of r3 calculations do not "clutter" the main code of r3, to make it more readable





Generic Macros and Quantities

Use these built-in constants

```
`M E
                    е
     `M LOG2E
                    log2(e)
     `M_LOG10E
                    log10(e)
    `M LN2
                    ln(2)
    `M_LN10
                    ln(10)
     `M PI
                    рi
     `M TWO PI
                    pi*2.0
     `M_PI_2
                    pi/2.0
//
    `M_PI_4
                    pi/4.0
    `M 1 PI
                    1.0/pi
    `M 2 PI
                    2.0/pi
                    2.0/sqrt(pi)
    `M_2_SQRTPI
   `M_SQRT2
                    sqrt(2.0)
//
    `M_SQRT1_2
                    1.0/sqrt(2.0)=sqrt(0.5)
    `P CELSIUS0
                    273.15
//
     `P EPS0
                    8.854187817e-12
```





Generic Macros and Quantities (2)

Do not use other physical constants, they change over time

```
`define QQ_NIST2004
                          1.60217653e-19
                                                  // (NIST2004)
`define KB_NIST2004
                          1.3806505e-23
                                                  // (NIST2004)
`define EPS_OX
                          3.45313324863e-11
                                                  // `P_EPS0*3.90 (F/m)
`define EPS SI
                          1.035939974589e-10
                                                  // `P EPSO*11.7 (F/m)
`define oneSixth
                          0.1666666666666667
`define oneThird
                          0.3333333333333333
`define twoThirds
                          0.6666666666666667
```

- Compiler should optimize (pre-compute) things like 1.0/6.0
 - but don't bank on it
- Include > 16 digits
 - why?





Generic Macros and Quantities (3)

- Clipping/clamping macros
 - to enforce parameter ranges
 - to limit values for voltages and temperature
 - to prevent numerical evaluation problems, help convergence
 - clipping done with an "if" condition so not C_∞ smooth
 - computationally efficient, does not "warp" behavior in normal range
 - clipping ranges of 0.1 and 1.0 for voltages, temperature
 - smooth and hard clamping provided
- Standard parameter declaration types
 - documentation automatically generated from these
- Macros for simulation variables often used in models





Generic Macros and Quantities (4)

- Linearized exponential
 - to prevent numerical computation issues
 - physically something else will always limit currents/charges
 - e.g. parasitic series resistance
- collapsibleR macro
 - if a resistor value is changed from a "normal" value to zero (or a very small value), the formulation should be changed from a current contribution to a voltage contribution
 - implicitly adds an extra system variable (the current)
 - dynamically changing formulation is tricky, not standardized
 - hopefully this may become standard, but could change





Junction Macros

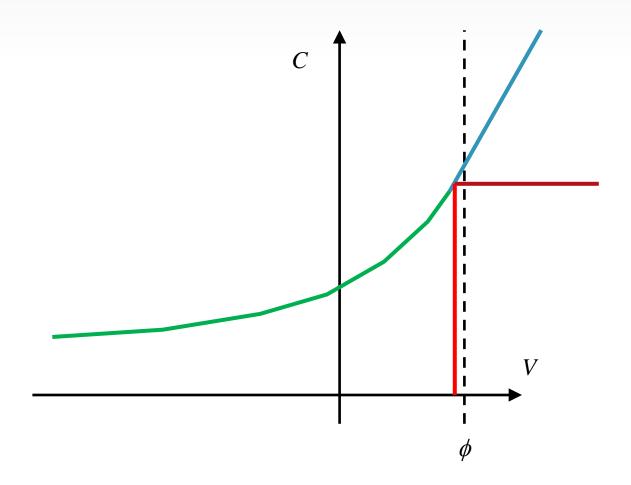
- pn-junctions found in many semiconductor devices
 - core (e.g. diodes, BJTs)
 - parasitic (e.g. MOS transistors)
- No point in every compact model re-inventing the wheel
 - these macros intended to help avoid that
- Junction depletion charge at forward bias
 - what happens when V approaches or exceeds ϕ ?

$$C_{depl} = \frac{C_0}{\left(1 - \frac{V}{\phi}\right)^m}$$





Junction Macros (2)







Junction Macros (3)

- Linear extrapolation is general SPICE approach
- Flattening off is used in some models
- Physically what happens is $C_{\it depl}$ peaks and then drops smoothly to zero
 - but this can cause convergence problems
- Gets overwhelmed by diffusion charge (exponential in V) so doesn't really matter
- Junction macros include all three approaches
 - with selectable hard or smooth transition
 - with selectable non-zero or zero value for V=0
 - latter is more computationally expensive, but needed for Early effect modeling for BJTs





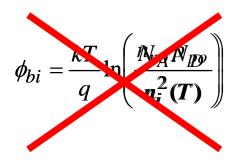
Junction Macros (4)

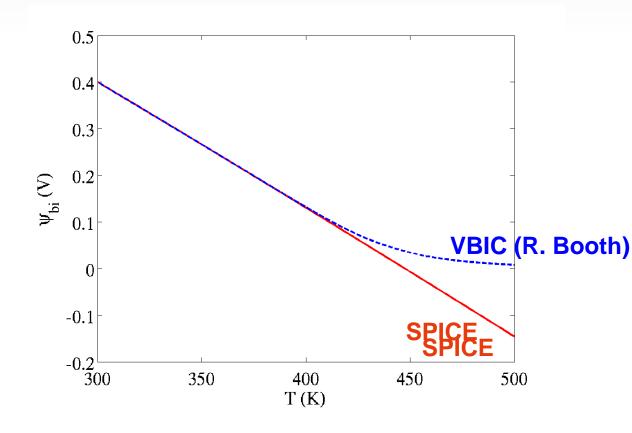
- Also includes
 - junction area/perimeter component current and charge models
 - junction breakdown model
 - proper junction shot noise model
 - asymptotically correct junction built-in potential temperature mapping





Junction Macros (4)









• Let's go through the code now





Macro for core R3 Calculation

- Basically separates all of the tricky and complex code for model evaluation
- Much of it is one-to-one with expressions derived in the "physics of r3" slides
 - part of homework assignment is to identify those
 - two most complex parts are handling pinch-off and computing the saturation voltage
 - do not worry about details of pinch-off computations
 - only relevant for JFETs





V_{sat} Calculation

- Complex part of the model
 - transitions to drain pinch-off and full pinch-off must be smooth
 - smoothing/interpolation function used maintains symmetry

$$V_{sat} \text{ is solution of } \frac{\partial}{\partial V} \left(V \frac{1 - d_f \sqrt{d_{pe} + V}}{\frac{V}{1 + \frac{V}{E_{cr}}}} \right) = 0 \quad \text{where} \quad d_{pe} = d_p - 2V_{c1}, \quad L_{DE} = L(E_{cr} - E_{co})$$

$$\frac{d_f^2}{4L_{DE}^2}V_{sat}^4 + \frac{3d_f^2}{2L_{DE}}V_{sat}^3 + d_f^2\left(\frac{9}{4} + \frac{p_e}{L_{DE}}\right)V_{sat}^2 + \left(3d_f^2 p_e - 1\right)V_{sat} + p_e\left(d_f^2 p_e - 1\right) = 0$$



A quartic equation,

by substituting for y the value, $x - \frac{p}{2}$ Here



$$x^4 + ax^3 + bx^2 + cx + d = 0,$$

V_{sat} Calculation (has the resolvent cubic equation

$$\frac{d_f^2}{4L_{DE}^2}V_{sat}^4 + \frac{3d_f^2}{2L_{DE}}V_{sa}^3$$

$$V_{sat}^3 + d_{sat}^2$$

A cubic equation
$$y^3 + py^2$$

For solution let .-

then the values o(x) will be given by,

$$y^{3} - by^{2} + (ac - 4d)y - a^{2}d + 4bd - c^{2} =$$

 $y^{3} + py^{2} + qy + r = 0$ may be reduced to the form,—
 $x^{3} + ax + b = 0$

 $a = \frac{1}{3}(3q - p^2)$ and $b = \frac{1}{27}(2p^3 - 9pq + 27r)$.

 $+\sqrt{\frac{b^2}{4}+\frac{a^3}{27}}, \qquad B=\sqrt[3]{-\frac{b}{2}}$

+ B, $-\frac{A+B}{2} + \frac{A-B}{2} \sqrt{-3}$, $-\frac{A+B}{2} - \frac{A-B}{2} \sqrt{-3}$.

a0 =
$$dfsq*dpe*d$$

a1 = $-1.0+3.0*df$
a2 = $dfsq*(9.0)$

cvar =
$$a1*a4i$$

1.5*dfsa

4.0*lde*ld

bb =
$$rvar-pvar*(qvar+2.0*aa)/9.0; \$$

$$aa3d27 = aa*aa*aa/27.0;$$

$$dd = 0.25*bb*bb+aa3d27; \$$

$$sd = sqrt(dd); \setminus$$



- Simple QA test specification, and code to run simulations, is provided with r3
- This is CMC QA code

